'Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2589	(118/500,501).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 16:50
L2	703	(semiconductor\$1 or wafer\$1) and cup same drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
L3	25	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:55
L4	46	(semiconductor\$1 or wafer\$1) and catch\$3 same cup same drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:55
L6	0	1 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
L7	822	(semiconductor\$1 or wafer\$1) and cup same (drain\$1 or drip\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
L8	25	1 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
S2	176	(yewebdar or tadesse) and ("118"/\$. ccls. or "264"/\$.ccls.)	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:07
S77	12	(("6,432,199") or ("5,705,223") or ("5, 947,136") or ("5,762,709") or ("6,533, 864") or ("5,940,651")).PN. or ((2003/101929) or (2003/183250)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/25 16:07

S78	6	(("6,432,199") or ("5,705,223") or ("5, 947,136") or ("5,762,709") or ("6,533, 864") or ("5,940,651")).PN. or ((2003/101929) or (2003/183250)). CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:44
S84	1	("20030101929").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:12
S85	1	("20030183250").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:12
S86	8	(("6,432,199") or ("5,705,223") or ("20030101929") or ("5,947,136") or ("5,762,709") or ("6,533,864") or ("5, 940,651") or ("20030183250")).PN.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:44
S88	1	S86 and (catch\$3 and drain\$3 and trap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S89	0	S86 and de near gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:48
S90	0	S86 and de-gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:48
S91	293	(semiconductor\$1 or wafer\$1) and de near gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:32
S92	210	(semiconductor\$1 or wafer\$1) and de-gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:53
S93	11	(semiconductor\$1 or wafer\$1) and (de-gas\$3 same separat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:55

F 60.6	4000	(440/52 (42) (60) 6	110 000:10	00	055	2005/02/20 22 55
S94	1364	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/28 09:53
S95	20145	(semiconductor\$1 or wafer\$1) and (separat\$3 near5 (gas or fluid or liquid))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:56
S96	27	(semiconductor\$1 or wafer\$1) and (separat\$3 near5 (gas or fluid or liquid)) same liquid near trap	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:31
S97	25	S96 and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:02
S98	27	(semiconductor\$1 or wafer\$1) and (catch near cup) same drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S99	2	S98 and frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:38
S10 0	1	(semiconductor\$1 or wafer\$1) and (catch near cup) same frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:05
S10 1	1	(semiconductor\$1 or wafer\$1) and (catch near cup) same (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:06
S10 2	1253	(semiconductor\$1 or wafer\$1) and (cup) same (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07

S10 3	533	(semiconductor\$1 or wafer\$1) and (cup) near7 (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07
S10 4	348	(semiconductor\$1 or wafer\$1) and (cup) near3 (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07
S10 5	293	(semiconductor\$1 or wafer\$1) and (cup) near7 (frame)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:08
S10 7	15	(semiconductor\$1 or wafer\$1) and (cup) near7 (frame) and drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:08
S10 8	14	S98 and lip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 16:49
S10 9	0	S86 and solvent near bath	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S11 0	30	(semiconductor\$1 or wafer\$1) and (solvent near bath) same drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:50
S11 1	5	S110 and frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:39

S11 2	22	S110 and (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:55
S11 3	5	(semiconductor\$1 or wafer\$1) and (solvent near bath) same drain\$1 same (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 12:00
S11 4	31	(semiconductor\$1 or wafer\$1) and (solvent near bath) same (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 12:02
S11 5	11	(semiconductor\$1 or wafer\$1) and (solvent near bath) near5 (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 11:10
S11 6	1037	(430/327).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/02 16:50
S11 7	51	nguyen-andrew\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 16:50
S11 8	1433	(427/240).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/03 10:39
S11 9	2	jp-2002151376\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 10:40
S12 0	2	("20020053319").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/03 10:44

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S12 1	11	(semiconductor\$1 or wafer\$1) and (solvent near bath) near5 (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 15:21
S12 2	124	(semiconductor\$1 or wafer\$1) and (wash\$3 or clean\$3)near5 (head\$1 or nozzle\$1)same (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 15:23
S12 3	13	(semiconductor\$1 or wafer\$1) and (wash\$3 or clean\$3)near5 (head\$1 or nozzle\$1)near7 (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 09:24
S12 4	807	(118/302).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 09:24
S12 5	643	(118/319).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 09:26
S12 6	628	(239/104,106).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 09:26
S12 7	6	(semiconductor\$1 or wafer\$1) and catch\$3 near5 cup same lip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:50